



THE DATASHEET OF ZVP3306FTC



ZVP33306F

SOT23 P-CHANNEL ENHANCED MODE VERTICAL DMOS FET ISSUE 3 – JANUARY 1996

FEATURES

- * 60 Volt V_{DS}
- * $R_{DS(on)} = 14\Omega$

PARTMARKING DETAIL – ML
COMPLEMENTARY TYPE – ZVN33306F

ABSOLUTE MAXIMUM RATINGS

PARAMETER

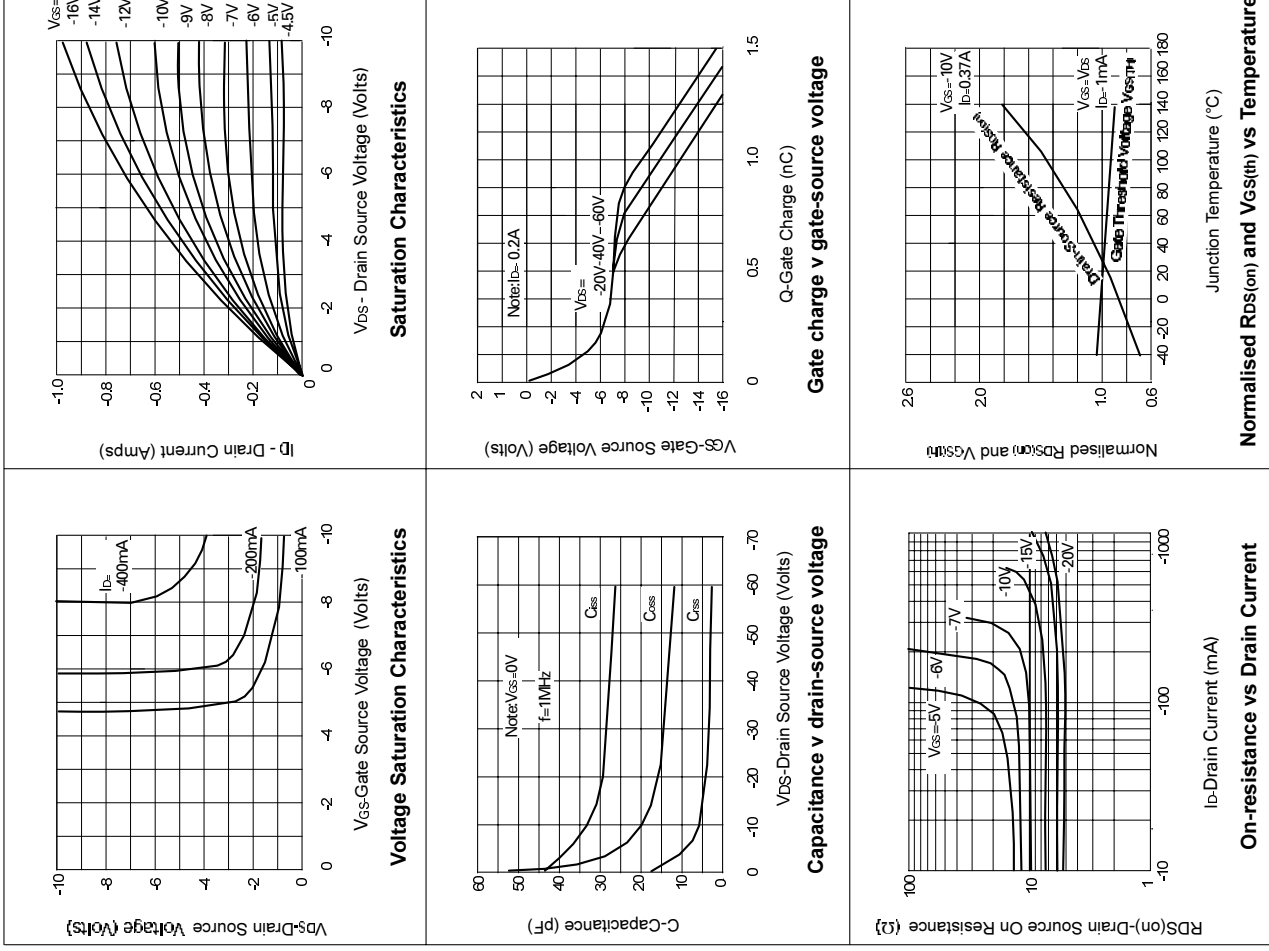
Drain-Source Voltage	
Continuous Drain Current at $T_{amb}=25^\circ\text{C}$	
Pulsed Drain Current	
Gate Source Voltage	
Power Dissipation at $T_{amb}=25^\circ\text{C}$	
Operating and Storage Temperature Range	

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL
Drain-Source Breakdown Voltage	BV_{DSS}
Gate-Source Threshold Voltage	$V_{GS(th)}$
Gate-Body Leakage	I_{GSS}
Zero Gate Voltage Drain Current	I_{DSS}
On-State Drain Current(1)	$I_{D(on)}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$
Forward Transconductance (1)(2)	g_{fs}
Input Capacitance (2)	C_{iss}
Common Source Output Capacitance (2)	C_{oss}
Reverse Transfer Capacitance (2)	C_{rss}
Turn-On Delay Time (2)(3)	$t_{d(on)}$
Rise Time (2)(3)	t_r
Turn-Off Delay Time (2)(3)	$t_{d(off)}$
Fall Time (2)(3)	t_f

(1) Measured under pulsed conditions. $W_{jmax} = 100^\circ\text{C}$.
 (2) Measured at $V_{GS} = 10\text{V}$, $I_D = 1\text{mA}$.
 (3) Switching times measured with 50Ω source and load. Spice parameter data is available upon request.

TYPICAL CHARACTERISTICS



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ABSOLUTE MAXIMUM RATINGS

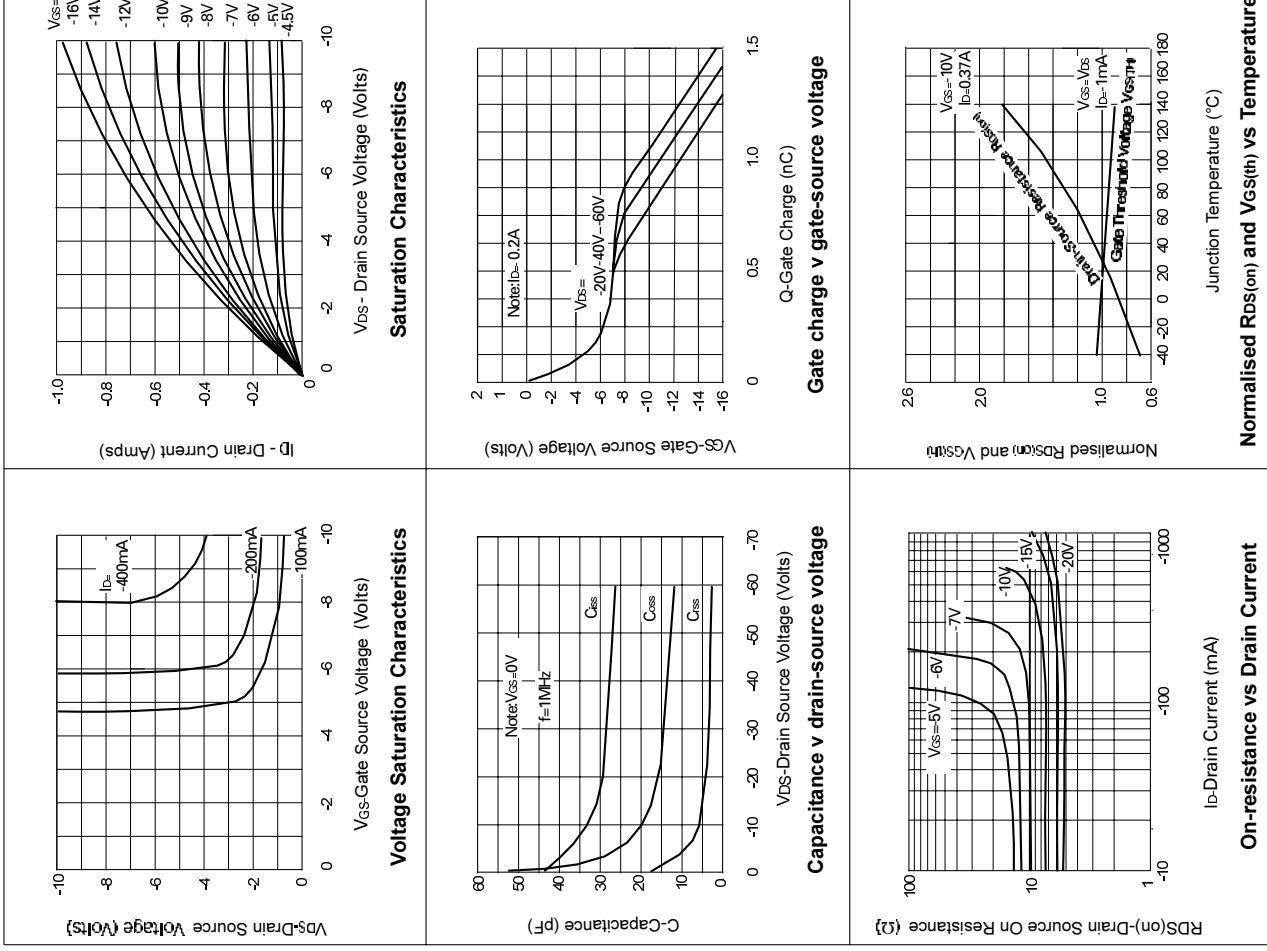
PARAMETER	SYMBOL
Drain-Source Voltage	BV_{DSS}
Continuous Drain Current at $T_{amb}=25^\circ\text{C}$	$I_{D(on)}$
Pulsed Drain Current	$I_{D(on)}$
Gate Source Voltage	$V_{GS(th)}$
Power Dissipation at $T_{amb}=25^\circ\text{C}$	I_{GSS}
Operating and Storage Temperature Range	I_{DSS}

ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL
Drain-Source Breakdown Voltage	BV_{DSS}
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(1) Measured under pulsed conditions. W_{ic}
(2) Switching times measured with 50Ω so
(3) Spice parameter data is available upon request

TYPICAL CHARACTERISTICS



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